TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

# SSM3K03FE

High Speed Switching Applications Analog Switch Applications

- 2.5 V gate drive
- High input impedance
- Low gate threshold voltage:  $V_{th} = 0.7 \sim 1.3 \text{ V}$
- Small package

## Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V <sub>DS</sub>	20	V
Gate-source voltage	V <sub>GSS</sub>	10	V
DC drain current	۱ <sub>D</sub>	100	mA
Drain power dissipation	PD	100	mW
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

1.6 ± 0.1 0.85 ± 0.1 0.27 0.5 0.5 6±0. .0∓0.1  $0.13 \pm 0.05$ GATE 1. SOURCE 2. ESM 3. DRAIN JEDEC \_ JEITA \_\_\_\_\_ TOSHIBA 2-2HA1B

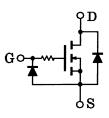
Weight: 2.3 mg (typ.)

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### Marking



### **Equivalent Circuit**



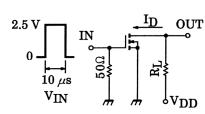
Unit: mm

**Electrical Characteristics (Ta = 25°C)** 

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS} = 10 \text{ V}, \text{ V}_{DS} = 0$	_		1	μA
Drain-source breakdown voltage		V (BR) DSS	$I_D = 100 \ \mu A, \ V_{GS} = 0$	20	_	_	V
Drain cut-off curre	ent	I <sub>DSS</sub>	$V_{DS} = 20 V, V_{GS} = 0$	_	_	1	μA
Gate threshold vo	ltage	V <sub>th</sub>	$V_{DS} = 3 \text{ V}, \text{ I}_{D} = 0.1 \text{ mA}$	0.7		1.3	V
Forward transfer a	admittance	Y <sub>fs</sub>	$V_{DS} = 3 \text{ V}, \text{ I}_{D} = 10 \text{ mA}$	25	50		mS
Drain-source ON	resistance	R <sub>DS (ON)</sub>	$I_D = 10 \text{ mA}, V_{GS} = 2.5 \text{ V}$	_	4	12	Ω
Input capacitance		C <sub>iss</sub>	$V_{DS} = 3 V, V_{GS} = 0, f = 1 MHz$	_	11.0		pF
Reverse transfer	capacitance	C <sub>rss</sub>	$V_{DS} = 3 V, V_{GS} = 0, f = 1 MHz$	_	3.3		pF
Output capacitance		C <sub>oss</sub>	$V_{DS} = 3 V, V_{GS} = 0, f = 1 MHz$	_	9.3		pF
Switching time	Turn-on time	t <sub>on</sub>	$V_{DD} = 3 \text{ V}, \text{ I}_{D} = 10 \text{ mA}, \text{ V}_{GS} = 0 \sim 2.5 \text{ V}$	_	0.16		μS
	Turn-off time	t <sub>off</sub>	$V_{DD} = 3 \text{ V}, \text{ I}_{D} = 10 \text{ mA}, \text{ V}_{GS} = 0 2.5 \text{ V}$	_	0.19		

## Switching Time Test Circuit

(a) Test circuit

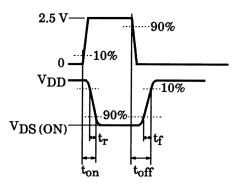


 $\begin{array}{c|c} \underline{ID} & \underline{OUT} & \underline{VDD} = 3 \ V \\ \hline & D.U. \leq 1\% \\ \hline & V_{IN} : t_r, \ t_r < 5 \ ns \\ \hline & (Z_{out} = 50 \ \Omega) \\ \hline & COMMON \ SOURCE \\ \hline & V_{DD} & Ta = 25^{\circ}C \end{array}$ 

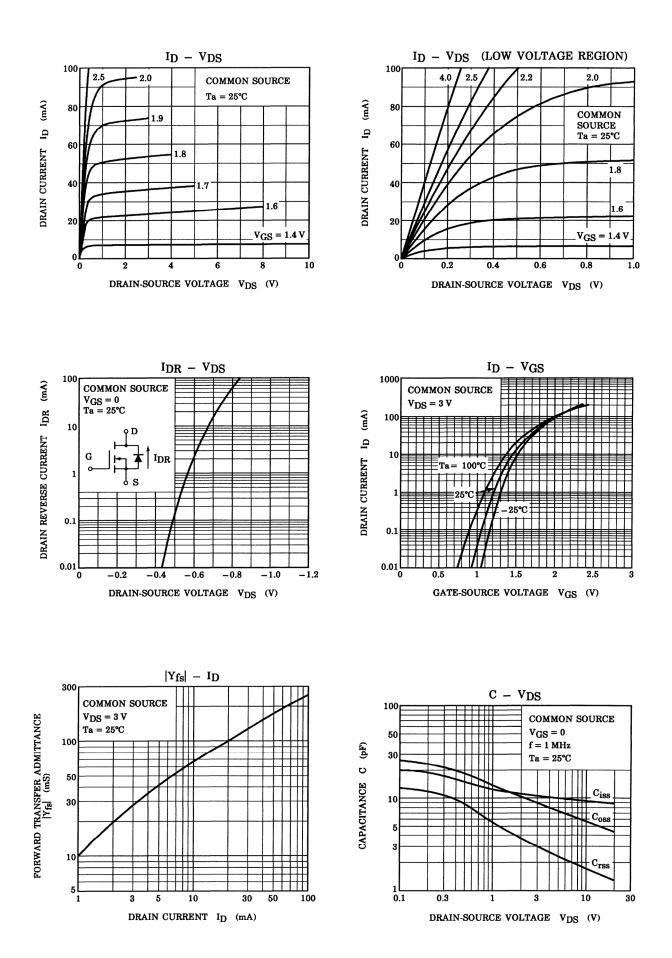
(b) V<sub>IN</sub> V<sub>GS</sub>

Vout

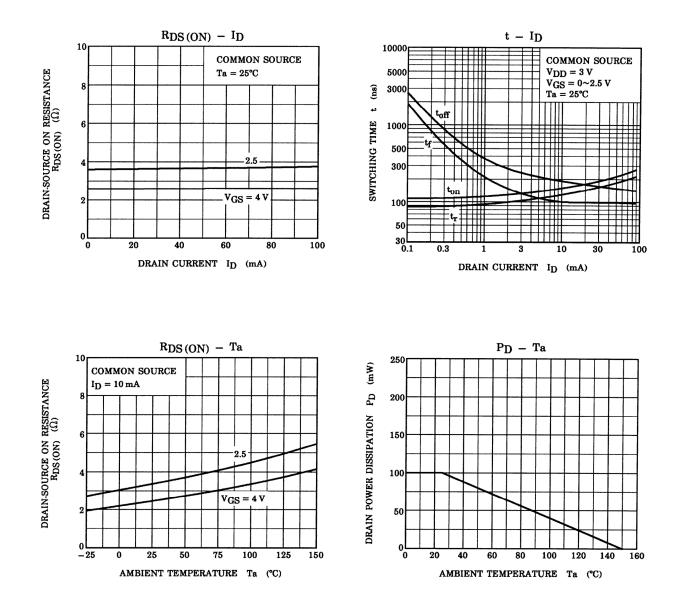
VDS



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20070701-EN GENERAL

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